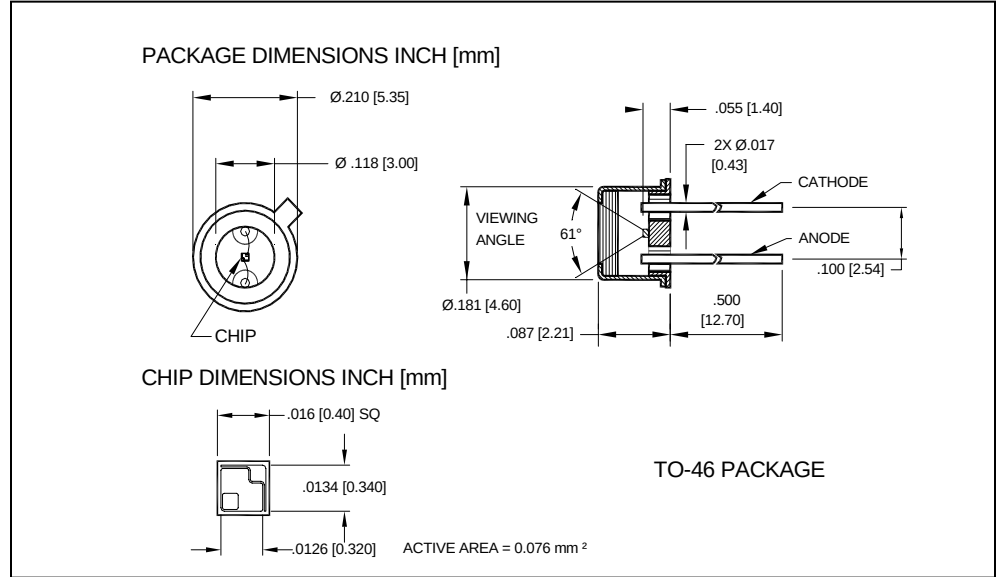




FEATURES

- 320nm UVB response
- Visible & NIR blind
- Photovoltaic operation
- High shunt resistance

DESCRIPTION

The **PDU-G102B** is a GaN UV photodiode with a spectral range from 200nm to 320nm and is ideal for UVB sensing applications available in a TO-46 can package.

APPLICATIONS

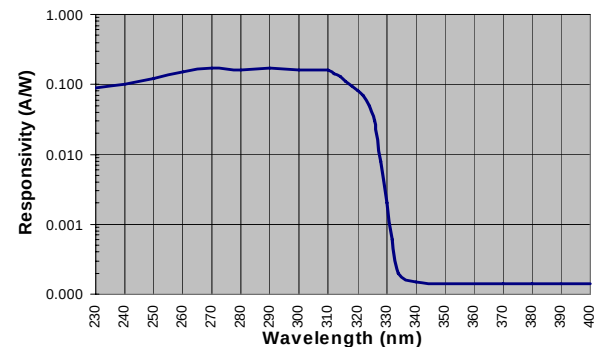
- UVB power meters
- Sun dosimeters
- UV epoxy curing
- UV instrumentation

ABSOLUTE MAXIMUM RATING (TA= 23°C UNLESS OTHERWISE NOTED)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		5	V
T _{STG}	Storage Temperature	-40	+90	°C
T _O	Operating Temperature	-30	+85	°C
T _S	Soldering Temperature*		+260	°C

* 1/16 inch from case for 3 seconds max.

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS RATING (TA= 23°C UNLESS OTHERWISE NOTED)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{SC}	Short Circuit Current	UVI = 1		1		nA
I _D	Dark Current	V _R = 1V		0.05	1	nA
R _{SH}	Shunt Resistance	V _R = 10 mV	0.45	1		GΩ
C _J	Junction Capacitance	V _R = 0V, f = 1 MHz		24		pF
λ _{range}	Spectral Application Range	Spot Scan	200		320	nm
R	Responsivity	λ = 350nm V, V _R = 0 V		0.10		A/W
V _{BR}	Breakdown Voltage	I = 1 μA		10		V
t _r	Response Time	RL = 1KΩ, V _R = 1V		10	15	nS